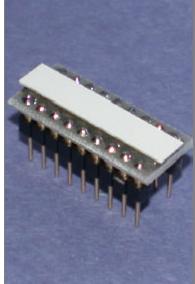
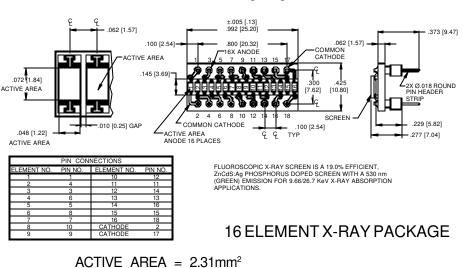
PHOTONIC <u>DETECTORS INC.</u>



X-RAY, Silicon Photodiode Array, Photovoltaic (with scintillation screen) Type PDB-V216-S

PACKAGE DIMENSIONS INCH [mm]



FEATURES

- .062 inch centers
- Stackable
- Scintillation screen
- Low capacitance

DESCRIPTION The **PDB-V216-S** is a common cathode, monolithic silicon PIN photodiode 16 element array. Designed to be stacked end

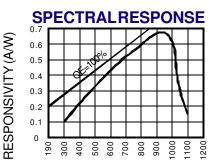
to end to form a line of pixels. Supplied with a fluoroscopic X-Ray scintillation screen.

APPLICATIONS

- Luggage X-ray
- X-Ray scanner
- X-Ray inspection

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS	
VBR	Reverse Voltage		50	V	
T _{STG}	Storage Temperature	-40	+100	с	
T _o	Operating Temperature Range	-20	+75	с	
Τ _s	Soldering Temperature*		+265	°C	
Ι _L	Light Current		500	mA	



WAVELENGTH(nm)

*1/16 inch from case for 3 secs max

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted, without scintillator)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS			
ع کا	Short Circuit Current	H = 100 fc, 2850 K	18	28		μA			
I _D	Dark Current	$H = 0, V_{R} = 1 V$		1.0	5.0	nA			
R _{SH}	Shunt Resistance	$H = 0, V_{R} = 10 \text{ mV}$	200	400		MΩ			
TC R _{SH}	RSH Temp. Coefficient	H = 0, V _R = 10 mV		-8		% / °C			
CJ	Junction Capacitance	$H = 0, V_{R} = 0 V^{**}$		300	400	рF			
λrange	Spectral Application Range	Spot Scan	350		1100	nm			
λρ	Spectral Response - Peak	Spot Scan		950		nm			
V _{BR}	Breakdown Voltage	I = 10 µµA	15	30		V			
NEP	Noise Equivalent Power	V _R = 10 V @ Peak		2x10 ⁻¹⁴		W/\sqrt{Hz}			
tr	Response Time	$RL = 50 \Omega V_R = 10 V$		50		nS			

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. ** f = 1 MHz [FORMNO.100-PDB-V216-SREVD]